

CFR §1.136 set out in the penultimate section ("Request for Extension of the Term for Response") hereof.

Please amend the application as follows:

In the Specification

Please amend the paragraph at page 6, lines 10-12 of the specification to read as follows:¹

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The high electron mobility of InN ($4000 \text{ cm}^2/\text{Vs}$ for $n=1\text{E}16 \text{ cm}^{-3}$) in relation to GaN permits the use of InGaN alloys in the channel layer of the device to achieve significant improvements in electrical properties and device performance.

In the Claims²

Cancel claims 11-34.

Amend claim 9, to read as follows:

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9. (Twice amended) The device of claim 7, wherein the AlGaN layer comprises a dopant providing an increased sheet density in relation to a corresponding undoped AlGaN layer.

Add new claims 35-42, as follows:

35. (new) The device of claim 1, wherein said InGaN alloy contains an amount of indium, $\text{In}/(\text{In}+\text{Ga})$, that does not exceed 0.20.

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¹ A marked-up version of the amended paragraph is set forth in Appendix A hereof.

² Consistent with the requirements of 37 CFR §1.121, a marked-up copy of the amended claim 9 is set forth in Appendix B herein. Consistent with the holding of *Festo Corp. v. Shoketsu Kinzoku Kogyo Kabushiki Co., Ltd., et al.*, 535 U.S. __ (2002), decided May 28, 2002, any amendments herein that hereafter are deemed to be narrowing amendments by a court of competent jurisdiction in a final unappealed or unappealable decision, are not intended to relinquish any scope of equivalents unforeseeable at the time of this amendment or that relate to aspects of the invention having only a peripheral relation to the basis of the amendment.